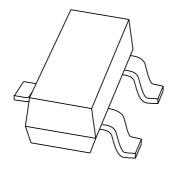
DISCRETE SEMICONDUCTORS

DATA SHEET



PMBD6050 High-speed diode

Product specification Supersedes data of 1999 May 11 2004 Jan 14





High-speed diode

PMBD6050

FEATURES

- Small plastic SMD package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 70 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA.

APPLICATIONS

• High-speed switching in thick and thin-film circuits.

DESCRIPTION

The PMBD6050 is a high-speed switching diode fabricated in planar technology, and encapsulated in a small SOT23 plastic SMD package.

MARKING

TYPE NUMBER	MARKING CODE(1)	
PMBD6050	*5A	

Note

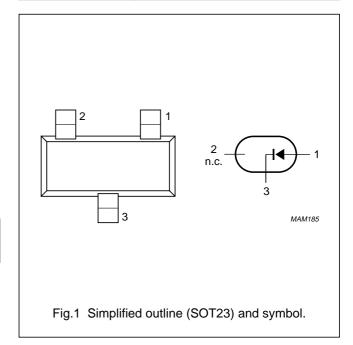
1. * = p : Made in Hong Kong.

* = t : Made in Malaysia.

* = W : Made in China.

PINNING

PIN	DESCRIPTION
1	anode
2	not connected
3	cathode



ORDERING INFORMATION

TYPE	PACKAGE		
NUMBER	NAME	DESCRIPTION	VERSION
PMBD6050	_	plastic surface mounted package; 3 leads	SOT23

High-speed diode

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{RRM}	repetitive peak reverse voltage		_	85	V
V_R	continuous reverse voltage		_	70	V
l _F	continuous forward current	note 1; see Fig.2	_	215	mA
I _{FRM}	repetitive peak forward current		_	500	mA
I _{FSM}	non-repetitive peak forward current	square wave; T _j = 25 °C prior to surge; see Fig.4			
		t = 1 μs	_	4	Α
		t = 1 ms	_	1	Α
		t = 1 s	_	0.5	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C; note 1	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C

Note

1. Device mounted on an FR4 printed-circuit board.

High-speed diode

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ELECTRICAL CHARACTERISTICS

 T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V _F	forward voltage	see Fig.3		
		I _F = 1 mA	715	mV
		I _F = 10 mA	855	mV
		I _F = 50 mA	1	V
		I _F = 150 mA	1.25	V
I_{R}	reverse current	see Fig.5		
		V _R = 50 V	100	nA
		V _R = 50 V; T _j = 150 °C	50	μΑ
C _d	diode capacitance	$f = 1 \text{ MHz}$; $V_R = 0$; see Fig.6	1.5	pF
t _{rr}	reverse recovery time	when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA; see Fig.7	4	ns
V _{fr}	forward recovery voltage	when switched from $I_F = 10$ mA; $t_r = 20$ ns; see Fig.8	1.75	V

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-tp)}	thermal resistance from junction to tie-point		330	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	500	K/W

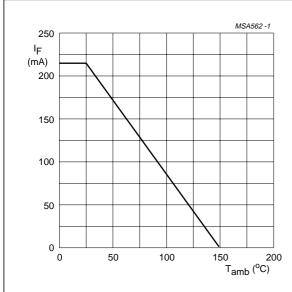
Note

1. Device mounted on an FR4 printed-circuit board.

High-speed diode

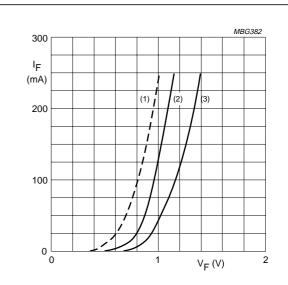
PMBD6050

GRAPHICAL DATA



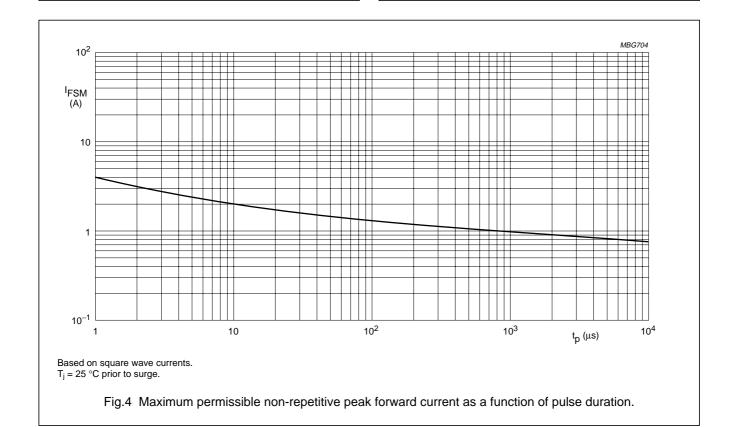
Device mounted on an FR4 printed-circuit board.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



- (1) $T_i = 150$ °C; typical values.
- (2) $T_j = 25$ °C; typical values.
- (3) T_j = 25 °C; maximum values.

Fig.3 Forward current as a function of forward voltage.

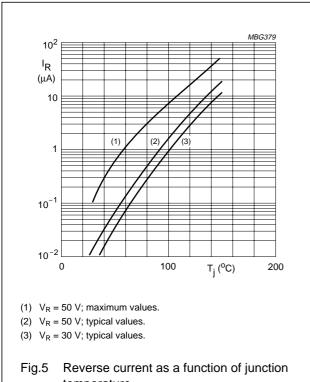


0.8

High-speed diode

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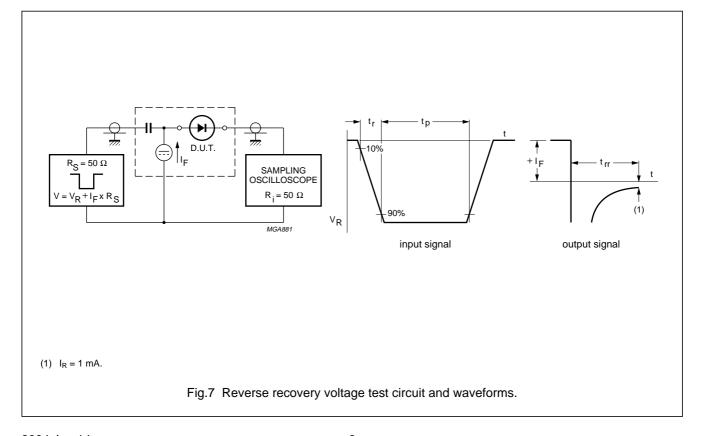
MBG446



C_d (pF) 0.6 0.4 0.2 12 $_{V_{R}}(V)$ 16 $f = 1 \text{ MHz}; T_j = 25 \,^{\circ}\text{C}.$

temperature.

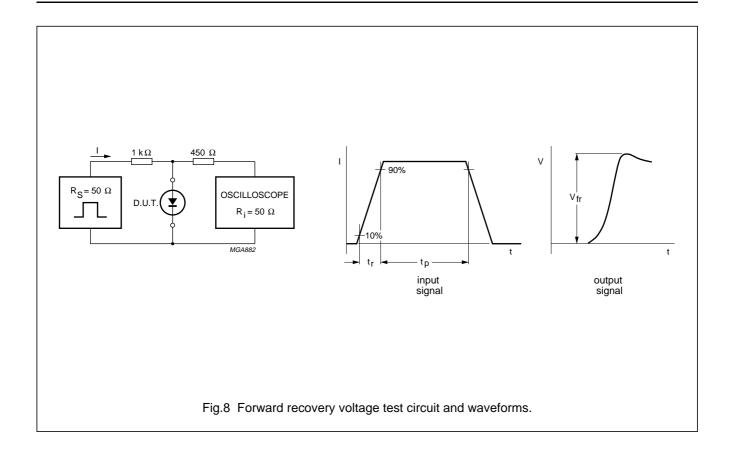
Fig.6 Diode capacitance as a function of reverse voltage; typical values.



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High-speed diode

PMBD6050



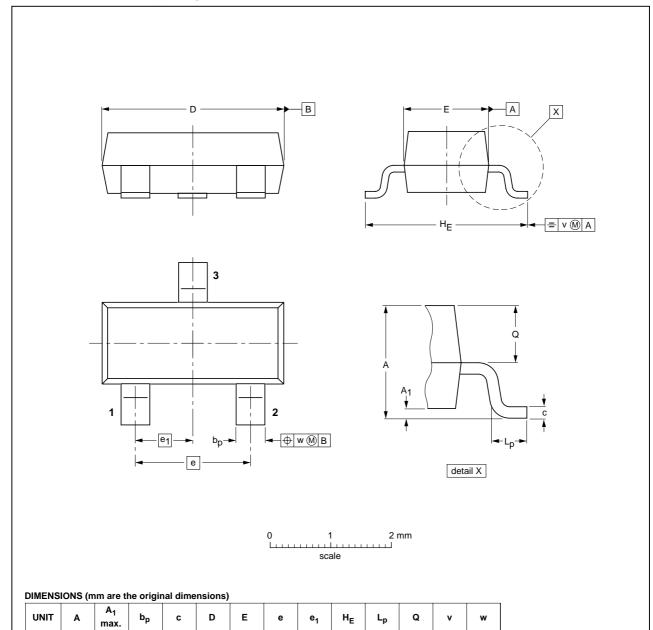
High-speed diode

PMBD6050

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT23		TO-236AB				97-02-28 99-09-13

0.95

1.9

0.45

0.55

0.2

0.1

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0.48

0.9

High-speed diode

PMBD6050

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
III	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

Notes

- 1. Please consult the most recently issued data sheet before initiating or completing a design.
- 2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.
- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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